

В. В. ДЕНИСЕНКО

**Компактные модели
МОП-транзисторов
для SPICE
в микро- и наноэлектронике**

В.В. Денисенко

Компактные модели МОП-транзисторов для SPICE в микро- и наноэлектронике



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Монография содержит систематическое изложение принципов построения компактных моделей МОП-транзисторов для схемотехнического моделирования электронных цепей, в том числе СБИС. Рассмотрены проблемы моделирования, физические процессы в микро- и нанометровых МОП-транзисторах, методы формирования уравнений компактных моделей, особенности моделей BSIM, EKV, PSP, HiSIM и др., табличные модели, полунатурные модели.

Для разработчиков интегральных схем и электронной аппаратуры, разработчиков САПР СБИС, научных работников и аспирантов. Может быть полезна студентам физических специальностей университетов.

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